

#### **Pin Definition:**

### **PRODUCT SUMMARY**

V <sub>CES</sub> (V)	V <sub>GES</sub> (V)	I <sub>C</sub> (A)
1200	±20	15

k <u>Diagram</u>

### **General Description**

The TSG15N120CN using proprietary trench design and advanced NPT technology, the 1200V NPT IGBT offers superior conduction and switching performances, high avalanche ruggedness and easy parallel operation. This device is well suited for the resonant or soft switching application such as induction heating, microwave oven, etc.

### **Features**

- 1200V NPT Trench Technology .
- **High Speed Switching** •
- Low Conduction Loss

### **Ordering Information**

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	<ul> <li>High Speed Switching</li> <li>Low Conduction Loss</li> </ul>	]		ent c
<u>(</u>	Ordering Informatio	<u>n</u>	4	Ģ V
	Part No.	Package	Packing	
	TSG15N120CN C0	TO-3PN	30pcs / Tube	٥E
-				NPT Trench IGBT

### Absolute Maximum Rating (T<sub>A</sub>=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Collector-Emitter Voltage		V <sub>CES</sub>	1200	V
Gate-Emitter Voltage		V <sub>GES</sub>	±20	V
	T <sub>C</sub> =25°C		30	А
Continuous Current	T <sub>c</sub> =100°C	I <sub>C</sub>	15	А
Pulsed Collector Current *		I <sub>CM</sub>	45	А
Diode Forward Current (T <sub>c</sub> =100 $^{\circ}$ C)		١ <sub>F</sub>	15	А
Diode Pulse Forward Current		I <sub>FM</sub>	45	А
Max Power Dissipation	T <sub>J</sub> =25°C		184	14/
	T <sub>J</sub> =100°C	PD	74	W
Operating Junction Temperature		TJ	-55 to +150	°C
Storage Temperature Range		T <sub>STG</sub>	-55 to +150	°C

\* Repetitive rating: Pulse width limited by max. junction temperature



#### **Thermal Performance**

Parameter			Limit	Unit
Thermel Desistance	IGBT		0.68	°C/W
Thermal Resistance - Junction to Case	DIODE	RO <sub>JC</sub>	3.7	
Thermal Resistance - Junction to Ambient		$R\Theta_{JA}$	40	

### Electrical Specifications (Tc=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_{C} = 1mA$	BV <sub>CES</sub>	1200			V
Zero Gate Voltage Collector Current	$V_{CE} = 1200V, V_{GE} = 0V$	I <sub>CES</sub>			1	mA
Gate-Emitter Leakage Current	$V_{GE}$ = 20V, $V_{CE}$ = 0V	I <sub>GES</sub>			±250	nA
Gate-Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 15mA$		3.0	5.0	7.0	V
Collector Emitter Seturation Valtage	V <sub>GE</sub> = 15V,I <sub>C</sub> =15A, T <sub>J</sub> =25°C	V <sub>CE(SAT)</sub>		1.9		V
Collector-Emitter Saturation Voltage	V <sub>GE</sub> = 15V,I <sub>C</sub> =15A, T <sub>J</sub> =125°C	V <sub>CE(SAT)</sub>		2.2		V
Dynamic	Q		-	-	-	
Input Capacitance		CIES		2650		
Output Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ f = 1.0MHz	C <sub>OES</sub>		150		pF
Reverse Transfer Capacitance		C <sub>RES</sub>		96		
Switching						
Turn-On Delay Time		t <sub>d(on)</sub>		34		
Rise Time		t <sub>r</sub>		106		nS
Turn-Off Delay Time	V <sub>CC</sub> = 600V, I <sub>C</sub> = 15A,	t <sub>d(off)</sub>		192		
Fall Time	R <sub>G</sub> = 10Ω, V <sub>GE</sub> = 15V	t <sub>f</sub>		94		
Turn-On Switching Loss	Inductive Load, T <sub>J</sub> =25°C	Eon		2.10		
Turn-Off Switching Loss		E <sub>off</sub>		0.54		mJ
Total Switching Loss		E <sub>ts</sub>		2.64		
Turn-On Delay Time		t <sub>d(on)</sub>		31		
Rise Time		t <sub>r</sub>		107		
Turn-Off Delay Time	$V_{\rm CC} = 600 V, I_{\rm C} = 15 A,$	t <sub>d(off)</sub>		204		nS
Fall Time	$R_{G} = 10\Omega, V_{GE} = 15V$	t <sub>f</sub>		86		
Turn-On Switching Loss	Inductive Load, T <sub>J</sub> =125°C	Eon		2.20		
Turn-Off Switching Loss		E <sub>off</sub>		0.93		mJ
Total Switching Loss		E <sub>ts</sub>		3.13		
Total Gate Charge		Qg		110		
Gate-Emitter Charge	$V_{\rm CC} = 600V, I_{\rm C} = 15A,$	Q <sub>ge</sub>		15		nC
Gate-Collector Charge	V <sub>GE</sub> = 15V	Q <sub>gc</sub>		40		



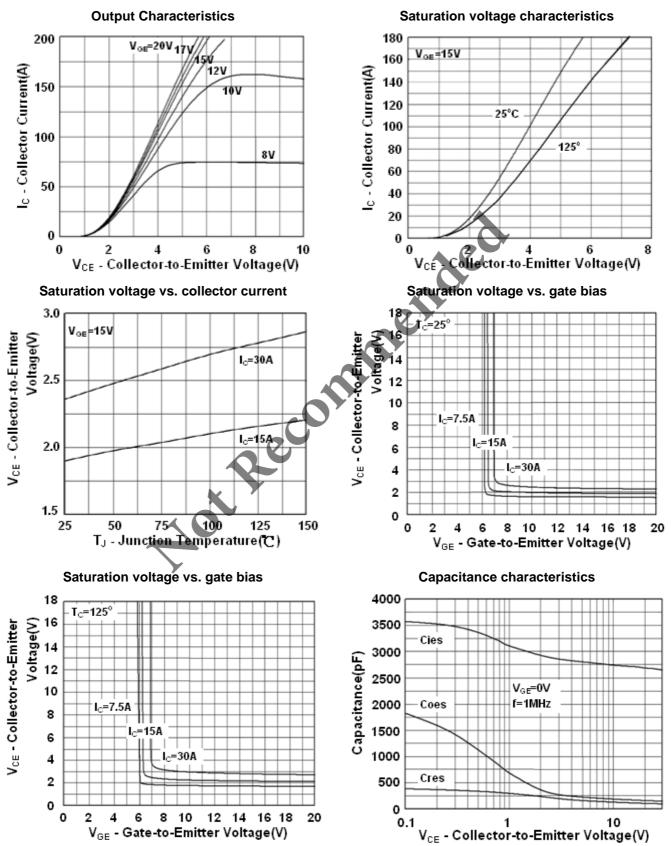
#### Electrical Specifications of the DIODE (Tc=25°C unless otherwise noted)

Parameter	Conditions		Symbol	Min	Тур	Max	Unit
		T <sub>J</sub> =25°C	$V_{FM}$	-	2.0	-	V
Diode Forward Voltage	I <sub>F</sub> = 15A,	T <sub>J</sub> =125°C		-	2.2	-	V
		T <sub>J</sub> =25°C	t <sub>fr</sub>		200		ns
Reverse Recovery Time		T <sub>J</sub> =125 <sup>°</sup> C			270		
Reverse Recovery Current	I <sub>F</sub> = 15A, dl/dt=200A/us	T <sub>J</sub> =25°C	I <sub>fr</sub>		22		A
		T <sub>J</sub> =125°C			28		
Reverse Recovery Charge		T <sub>J</sub> =25°C	Q <sub>fr</sub>		2230		nC
		T <sub>J</sub> =125°C			3750		

T\_=125°C Qr

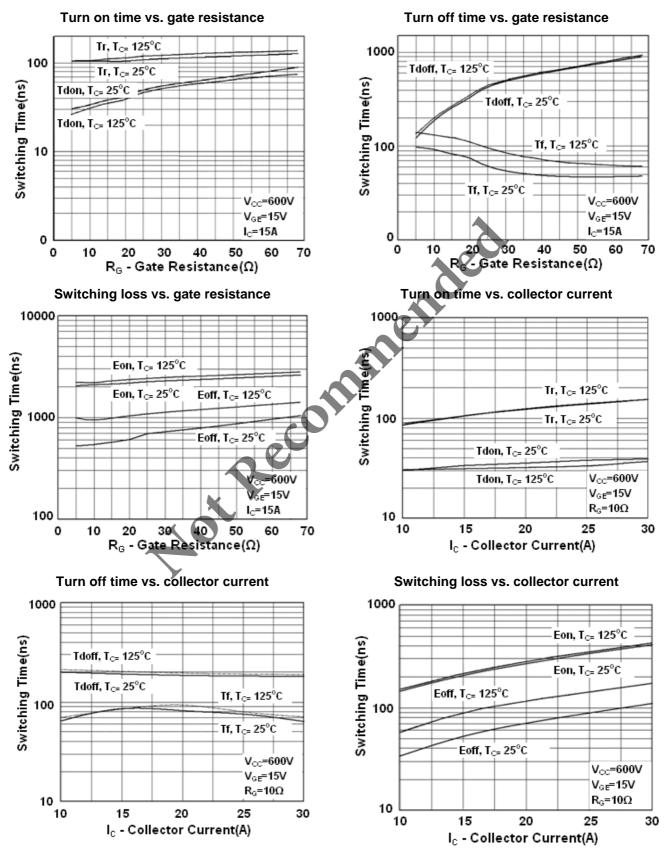


### Electrical Characteristics Curve (Tc = 25°C, unless otherwise noted)

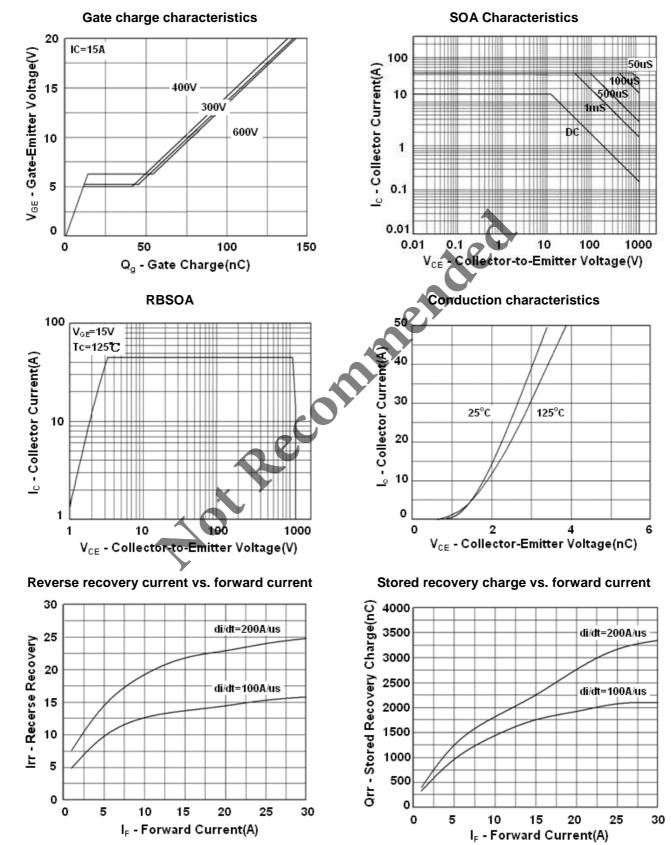




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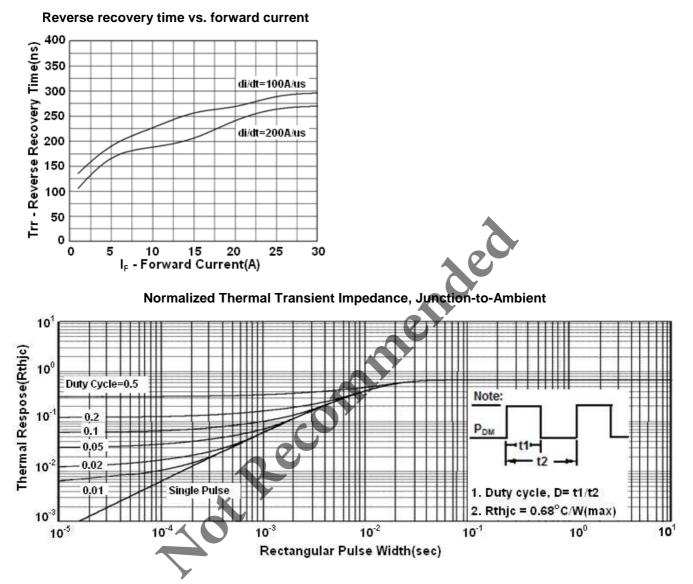




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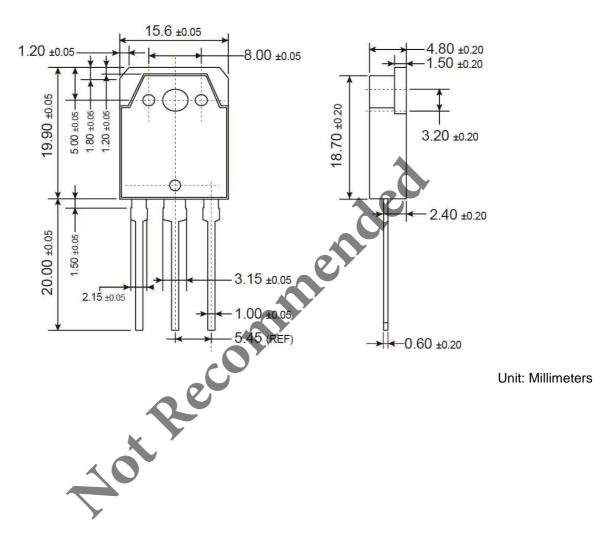


#### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)





### **TO-3PN Mechanical Drawing**







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